

PSMN7R0-100BS

N-channel 100V 6.8 m Ω standard level MOSFET in D2PAK.

Rev. 2 — 2 March 2012

Objective data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Mir	n Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	100	V
I_D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[1] -	-	100	Α
P_{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	269	W
T_j	junction temperature		-55	-	175	°C
Static cha	racteristics					
R_{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 ^{\circ}\text{C}; \text{see } \frac{\text{Figure } 12}{}$	-	-	12	$m\Omega$
	resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{see } \underline{\text{Figure } 13}$	-	5.4	6.8	mΩ
Dynamic o	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 50 \text{ V};$ see Figure 15; see Figure 14	-	36	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 50 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	125	-	nC
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} V_{GS} &= 10 \text{ V; } T_{j(init)} = 25 \text{ °C; } I_D = 100 \text{ A;} \\ V_{sup} &= 100 \text{ V; unclamped; } R_{GS} = 50 \Omega \end{split}$	-	-	315	mJ

^[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
PSMN7R0-100BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404				

4. Limiting values

Table 4. Limiting values

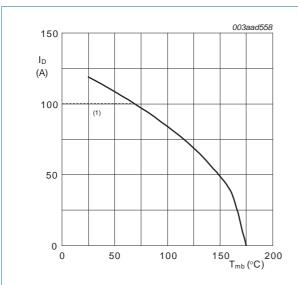
In accordance with the Absolute Maximum Rating System (IEC 60134).

$\begin{array}{c} V_{DGR} & drain\text{-gate voltage} & T_j \leq 175~^\circ\text{C}; \ T_j \geq 25~^\circ\text{C}; \ R_{GS} = 20~\text{k}\Omega & - & 100 \\ V_{GS} & gate\text{-source voltage} & -20 & 20 \\ I_D & drain current & V_{GS} = 10~\text{V}; \ T_{mb} = 100~^\circ\text{C}; \ see \ \underline{\text{Figure 1}} & - & 85 \\ \hline V_{GS} = 10~\text{V}; \ T_{mb} = 25~^\circ\text{C}; \ see \ \underline{\text{Figure 1}} & - & 100 \\ I_{DM} & \text{peak drain current} & \text{pulsed}; \ t_p \leq 10~\text{\mus}; \ T_{mb} = 25~^\circ\text{C}; \ see \ \underline{\text{Figure 3}} & - & 475 \\ P_{tot} & \text{total power dissipation} & T_{mb} = 25~^\circ\text{C}; \ see \ \underline{\text{Figure 2}} & - & 269 \\ \hline T_{stg} & \text{storage temperature} & -55 & 175 \\ \hline T_j & \text{junction temperature} & -55 & 175 \\ \hline T_{sld(M)} & \text{peak soldering temperature} & - & 260 \\ \hline \textbf{Source-drain diode} & & & & & & & & & \\ I_S & \text{source current} & T_{mb} = 25~^\circ\text{C} & \underline{11} & - & 100 \\ \hline I_{SM} & \text{peak source current} & \text{pulsed}; \ t_p \leq 10~\text{\mus}; \ T_{mb} = 25~^\circ\text{C} & - & 475 \\ \hline \textbf{Avalanche ruggedness} & & & & & & & & & & & \\ \hline \end{array}$	bol	Parameter	Conditions	Min	Max	Unit
$\begin{array}{c} V_{GS} & \text{gate-source voltage} \\ I_D & \text{drain current} \\ \\ V_{GS} = 10 \text{ V}; T_{mb} = 100 ^{\circ}\text{C}; \text{see Figure 1} \\ \\ V_{GS} = 10 \text{ V}; T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 1} \\ \\ I_{DM} & \text{peak drain current} \\ \\ P_{tot} & \text{total power dissipation} \\ T_{mb} = 25 ^{\circ}\text{C}; \text{see Figure 3} \\ \\ T_{stg} & \text{storage temperature} \\ \\ T_{j} & \text{junction temperature} \\ \\ T_{sld(M)} & \text{peak soldering temperature} \\ \\ Source-drain diode \\ \\ I_{S} & \text{source current} \\ \\ I_{SM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ I_{DM} & \text{peak source current} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^{\circ}\text{C} \\ \\ P_{ulsed}; t_{p} \leq 10 \mu \text{s}; T_{mb} = 25 ^$		drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$?	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
$V_{GS} = 10 \text{ V; } T_{mb} = 25 \text{ °C; see } \underline{\text{Figure 1}} \qquad \underbrace{11} - 100 \\ I_{DM} \qquad \text{peak drain current} \qquad \text{pulsed; } t_p \leq 10 \mu \text{s; } T_{mb} = 25 \text{ °C; see } \underline{\text{Figure 3}} \qquad - 475 \\ P_{tot} \qquad \text{total power dissipation} \qquad T_{mb} = 25 \text{ °C; see } \underline{\text{Figure 2}} \qquad - 269 \\ T_{stg} \qquad \text{storage temperature} \qquad \qquad -55 175 \\ T_j \qquad \text{junction temperature} \qquad \qquad -55 175 \\ T_{sld(M)} \qquad \text{peak soldering temperature} \qquad \qquad - 260 \\ \underline{\textbf{Source-drain diode}} \qquad \qquad \qquad - 260 \\ \underline{\textbf{Source-drain diode}} \qquad \qquad \qquad \qquad \qquad - 100 \\ I_{SM} \qquad \text{peak source current} \qquad \qquad T_{mb} = 25 \text{ °C} \qquad \qquad \qquad \boxed{11} - 100 \\ \underline{\textbf{Avalanche ruggedness}} \qquad \qquad \qquad \qquad \qquad - 475 \\ \underline{\textbf{Avalanche ruggedness}} \qquad \qquad$		gate-source voltage		-20	20	V
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$		drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	85	Α
$\begin{array}{cccccccccccccccccccccccccccccccccccc$			$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u> -	100	Α
T_{stg} storage temperature .55 175 T_{j} junction temperature .55 175 $T_{sld(M)}$ peak soldering temperature . 260 $T_{sld(M)}$ source-drain diode .50 $T_{mb} = 25$ °C .11 - 100 T_{mb} peak source current pulsed; $T_{mb} = 25$ °C . 475		peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	475	Α
T_j junction temperature		total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	269	W
$T_{sld(M)}$ peak soldering temperature - 260 Source-drain diode Source current T _{mb} = 25 °C 11 - 100 I _{SM} peak source current pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C - 475 Avalanche ruggedness		storage temperature		-55	175	°C
Source-drain diode $I_S \qquad \text{source current} \qquad T_{mb} = 25 ^{\circ}\text{C} \qquad \qquad \begin{array}{c} \text{[1]} - 100 \\ \\ I_{SM} \qquad \text{peak source current} \qquad \text{pulsed; } t_p \leq 10 \mu\text{s; } T_{mb} = 25 ^{\circ}\text{C} \qquad \qquad - 475 \\ \\ \text{Avalanche ruggedness} \end{array}$		junction temperature		-55	175	°C
I_S source current $I_{mb} = 25 ^{\circ}\text{C}$ $I_{mb} = 25 ^{\circ}\text{C}$ $I_{mb} = 25 ^{\circ}\text{C}$ - 100 I_{sm} peak source current pulsed; $I_p \le 10 \mu s$; $I_{mb} = 25 ^{\circ}\text{C}$ - 475 Avalanche ruggedness	Л)	peak soldering temperature		-	260	°C
I_{SM} peak source current pulsed; $t_p \le 10~\mu s$; $T_{mb} = 25~^{\circ}C$ - 475 Avalanche ruggedness	ce-drain c	diode				
Avalanche ruggedness		source current	T _{mb} = 25 °C	<u>[1]</u> -	100	Α
		peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	475	Α
$E_{DS(AL)S}$ non-repetitive drain-source $V_{GS} = 10 \text{ V}$; $T_{i(init)} = 25 \text{ °C}$; $I_D = 100 \text{ A}$; - 315	anche rug	gedness				
avalanche energy $V_{sup} = 100 \text{ V}$; unclamped; $R_{GS} = 50 \Omega$	AL)S	-	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} = 100 V; unclamped; R_{GS} = 50 Ω	-	315	mJ

^[1] Continuous current is limited by package.

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 $V_{GS} \ge 10 \text{ V}$; (1) capped at 100 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature

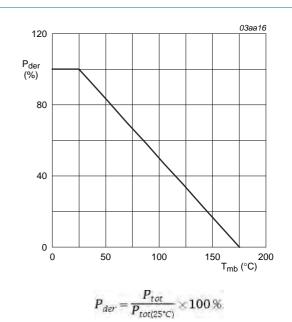
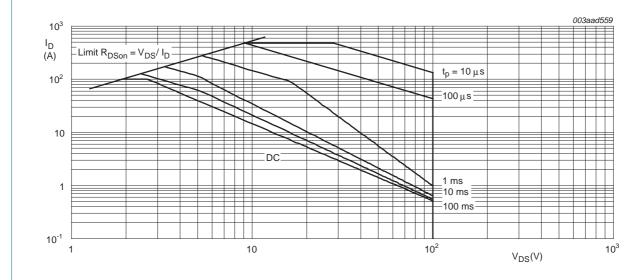


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25 \,^{\circ}C; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.56	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	60	-	K/W

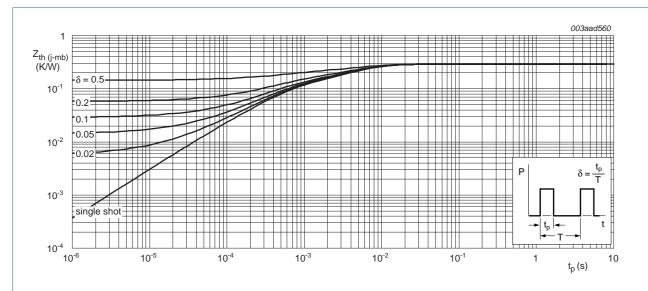


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS} drain-source		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.6	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	150	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.08	5	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	-	12	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12	-	15	19	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	5.4	6.8	mΩ
R_{G}	internal gate resistance (AC)	f = 1 MHz	-	0.74	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	125	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	100	-	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 15; see Figure 14	-	28	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 15	-	19.4	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	9	-	nC
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 15; see Figure 14	-	36	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	4.3	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	6686	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	438	-	pF
C_{rss}	reverse transfer capacitance		-	272	-	pF

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 2 \Omega; \text{ V}_{GS} = 10 \text{ V}; \\ \text{R}_{G(ext)} = 4.7 \Omega; \text{ T}_{j} = 25 \text{ °C}$	-	34.6	-	ns
t _r	rise time		-	45.6	-	ns
$t_{d(off)}$	turn-off delay time		-	103.9	-	ns
t _f	fall time		-	49.5	-	ns
Source-dra	in diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	64	-	ns
Q _r	recovered charge	$V_{DS} = 50 \text{ V}$	-	167	-	nC

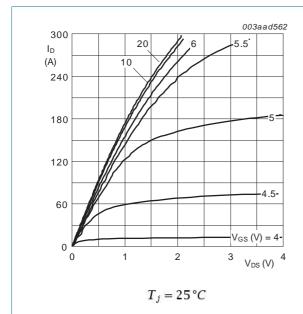


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

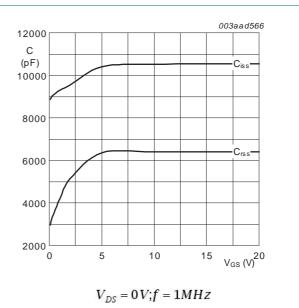


Fig 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

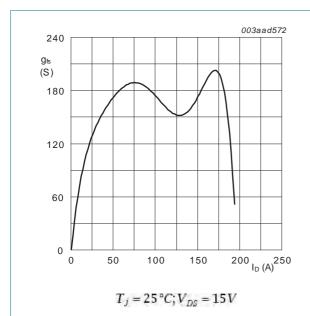


Fig 7. Forward transconductance as a function of drain current; typical values

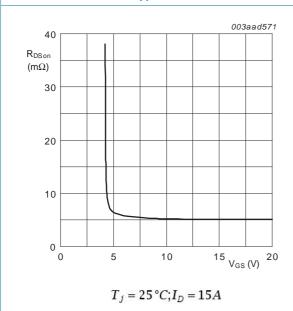


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

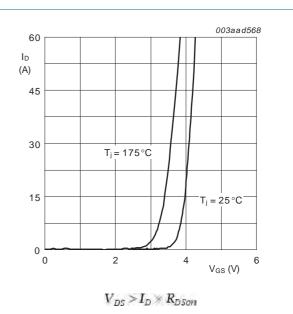


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

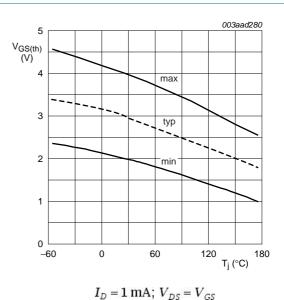


Fig 10. Gate-source threshold voltage as a function of junction temperature

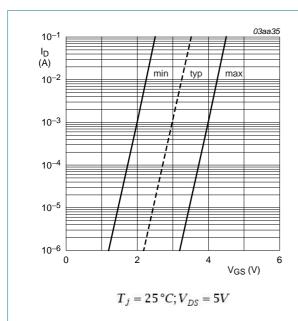


Fig 11. Sub-threshold drain current as a function of gate-source voltage

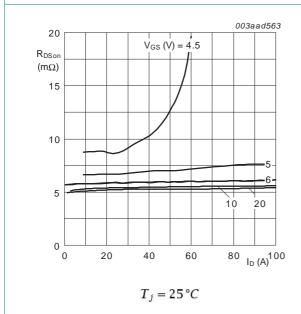


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

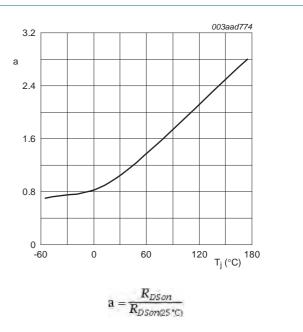


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

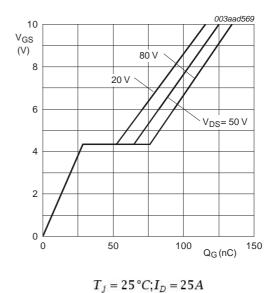
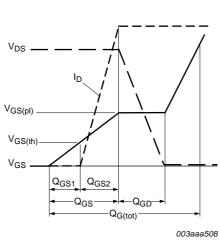


Fig 14. Gate-source voltage as a function of gate charge; typical values



003aaa508 003aaa508 $V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$

10⁴

C (pF)

10³

Fig 15. Gate charge waveform definitions



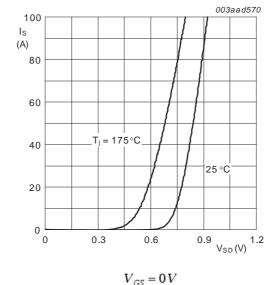


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

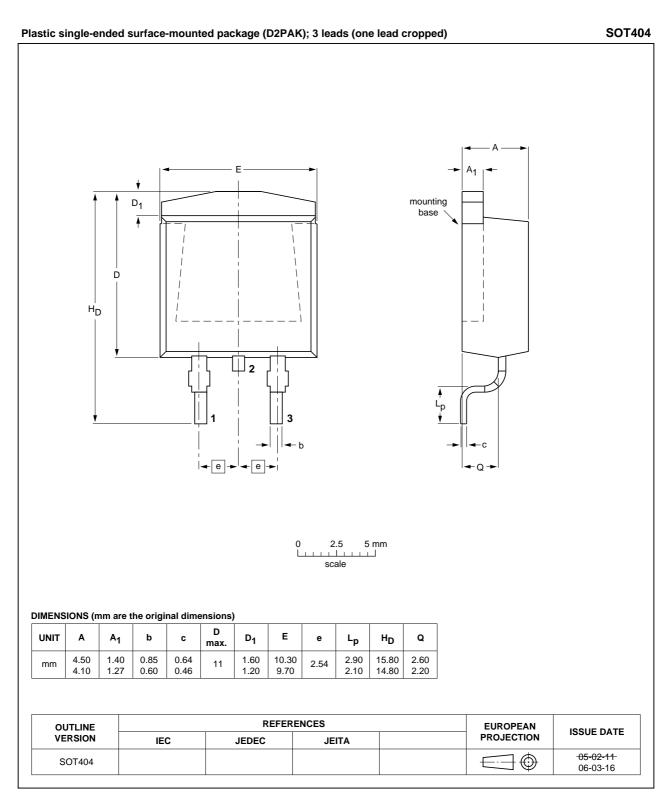


Fig 18. Package outline SOT404 (D2PAK)

Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN7R0-100BS v.2	20120302	Objective data sheet	-	PSMN7R0-100BS v.1
Modifications:	 Various changes to 	content.		
PSMN7R0-100BS v.1	20111025	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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PSMN7R0-100BS

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PSMN7R0-100BS

N-channel 100V 6.8 mΩ standard level MOSFET in D2PAK.

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10. Contact information

For more information, please visit:http://www.nexperia.com

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